

DARLINGTON POWER TRANSISTOR **2SA1841**

PNP SILICON EPITAXIAL TRANSISTOR (DARLINGTON CONNECTION) FOR HIGH-SPEED SWITCHING

The 2SA1841 is a high-speed Darlington power transistor. This transistor is ideal for high-precision control such as PWM control for pulse motors or brushless motors in OA and FA equipment.

In addition, this transistor features a package that can be auto-mounted in radial taping specifications, thus contributing to mounting cost reduction.

FEATURES

- · Auto-mounting possible in radial taping specifications
- · Resin-molded insulation type package with power rating of 1.8 W in stand-alone conditions
- High DC current amplifiers due to Darlington connection hFE = 4,000 to 20,000 @VcE = -2.0 V, Ic = -4.0 A
- On-chip C-to-E reverse diode
- · Fast switching speed

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Conditions	Ratings	Unit
Collector to base voltage	Vсво		-100	V
Collector to emitter voltage	VCEO		-100	V
Emitter to base voltage	VEBO		-8.0	V
Collector current (DC)	IC(DC)		-8.0	А
Collector current (pulse)	IC(pulse)	$PW \le 10 \text{ ms}$, duty cycle $\le 2\%$	-16	А
Base current (DC)	IB(DC)		-0.8	А
Total power dissipation	Рт	Ta = 25°C	1.8	w
Junction temperature	Tj		150	°C
Storage temperature	Tstg		-55 to +150	°C

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = -100 \text{ V}, \text{ I}_{E} = 0$			-1.0	μA
Collector cutoff current	Іево	$V_{EB} = -5.0 \text{ V}, \text{ Ic} = 0$			-5.0	mA
DC current gain	hfe1*	Vce = -2.0 V, Ic = -4.0 A	4,000		20,000	_
DC current gain	hfe2*	$V_{CE} = -2.0 \text{ V}, \text{ Ic} = -8.0 \text{ A}$	500			-
Collector saturation voltage	V _{CE(sat)} *	$I_{\rm C} = -4.0 \text{ A}, I_{\rm B} = -4.0 \text{ mA}$			-1.5	V
Base saturation voltage	V _{BE(sat)} *				-2.0	V
Turn-on time	ton	Ic = -4.0 A		0.2		μs
Storage time	tstg	l _{B1} = −l _{B2} = −4.0 mA R∟ = 12.5 Ω, Vcc = −50 V		1.5		μs
Fall time	tr			0.7		μs

* Pulse test PW \leq 350 μ s, duty cycle \leq 2%

hfe CLASSIFICATION

Marking	L	к		
hfe2	4,000 to 10,000	8,000 to 20,000		

PACKAGE DRAWING (UNIT: mm)

TAPING SPECIFICATION

a

C

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Electrode Connection

- 1. Base
- 2. Collector
- 3. Emitter





TYPICAL CHARACTERISTICS (Ta = 25°C)



Collector Current Ic (A)

Collector to Emitter Voltage VCE (V)



SWITCHING TIME (ton, tstg, tr) TEST CIRCUIT



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